

METHOD OF FORMING FLASH MEMORIES WITH HIGH COUPLING
RATIO AND THE STRUCTURE OF THE SAME

Abstract of the Disclosure

The flash memory structure includes a substrate having trenches formed therein, a first dielectric layer and a first conductive layer are stacked on the substrate. Isolations are formed in the trenches and protruding over the surface of the substrate, wherein the first conductive layer is also protruded over the isolations. A second conductive layer is lying the surface of the first conductive layer and a second dielectric layer formed thereon. A third conductive layer is formed on the second dielectric layer. The floating gate is consisted of first conductive layer and the second conductive layer.